AZ Power Inc. Providing A to Z Power Solutions

S2D120V005E SiC Schottky Diode

Features:

- 1200V Schottky Diode •
- Zero Reverse Recovery Current .
- High Frequency Operation •
- Positive Temperature Coefficient •
- Temperature independent • Switching

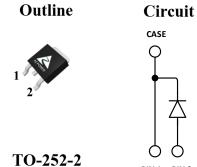
Applications:

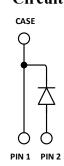
- Switch Mode Power Supply •
- Booster diodes in PFC, DC/DC •
- AC/DC converters

Benefits:

- Unipolar Rectifier •
- Minimal switching loss .
- Higher Efficiency •
- Low cooling requirement •

Symbol	Value	Unit		
V _{RRM}	1200	V		
$I_F \ (\text{Te}=155^{\circ}C)$	5	А		
Qc	27	nC		





Symbol	Parameter	Value	Unit	Test Conditions
VR	DC Peak Reverse Voltage	1200	V	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	1200	V	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	1300	V	$T_J = 25^{\circ}C$
IF	Continuous Forward Current	17.5 9.5 5	А	$T_{C} = 25^{\circ}C$ $T_{C} = 135^{\circ}C$ $T_{C} = 155^{\circ}C$
I _{FRM}	Repetitive Peak Forward Surge Current	24 17	А	$T_{\rm C}$ = 25°C, $T_{\rm P}$ = 10ms, Half Sine Wave Tc = 125°C, $T_{\rm P}$ = 10ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	55 51	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 125°C, $T_{\rm P} = 10$ ms, Half Sine Wave
PD	Power Dissipation	83 27	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
Tstg	Storage Temperature Range	-55 to 175	°C	

Maximum Ratings

S2D120V005E, Rev. 1.1

Page 1 of 4



Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
RthJC	Thermal resistance		1.8		°C/W

Electrical Characteristics

Symbol	value Value		Unit	Test Conditions		
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V _{DC}	DC Blocking Voltage	1200			V	$I_R = 100 \mu A, T_J = 25^{\circ}C$
V _F	Forward Voltage		1.55	1.8	V	$I_F = 5A, T_J = 25^{\circ}C$
v F	Forward Voltage		2.4	2.7		$I_{\rm F} = 5A, T_{\rm J} = 175^{\circ}{\rm C}$
I.	Reverse Current		1	100	μΑ	$V_{R} = 1200V, T_{J} = 25^{\circ}C$
I _R	Reverse Current		15	500		$V_R = 1200V, T_J = 175^{\circ}C$
0	Total Conscitive Change		27		nC	$I_{\rm F} = 5A, dI/dt = 200A/\mu s$
Qc	Total Capacitive Charge		27			$T_J = 25^{\circ}C, V_R = 800V$
			262			$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$
С	Total Capacitance		23		pF	V_R =400V, T_J =25°C, f=1 MHz
			19			V_R =800V, T_J =25°C, f=1 MHz

Typical Performance

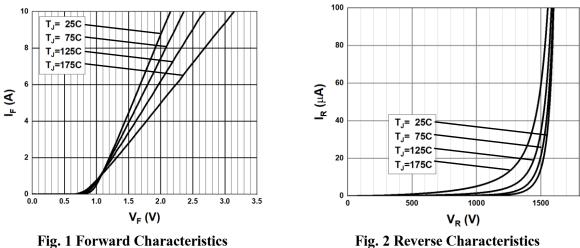


Fig. 2 Reverse Characteristics

0



Typical Performance

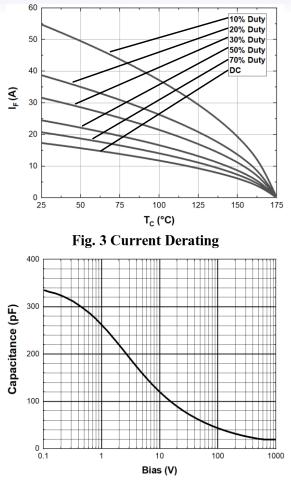


Fig. 5 Capacitance vs. Reverse Voltage

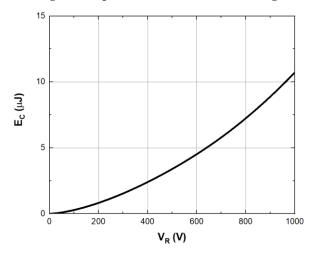


Fig. 7 Capacitance stored Energy

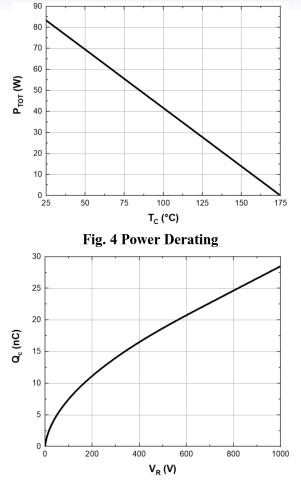


Fig. 6 Recovery Charge vs. Reverse Voltage

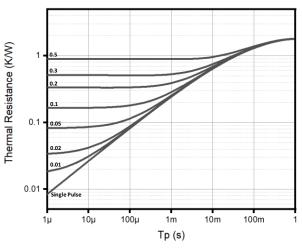
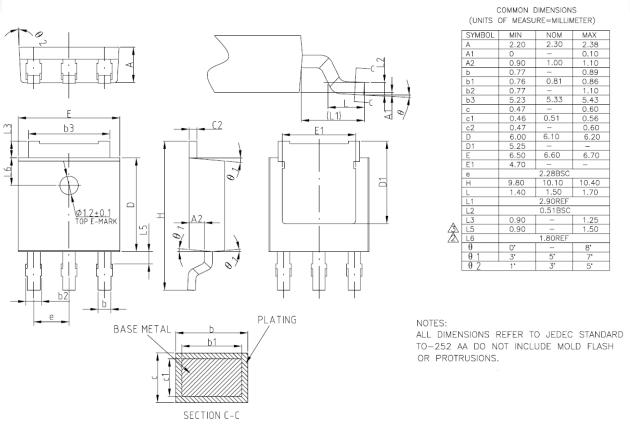


Fig. 8 Thermal Impedance



Package TO-252-2 (Unit: mm)



This Product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, systems, or air-traffic control systems.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, AZ Power Inc. disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.



5601 W SLAUSON AVE 190 CULVER CITY, CA 90230 WWW.AZPE.COM

Information in this document may change without notice. All referenced product or service names and trademarks are the property of their respective owners. Copyright © 2020 AZ Power Inc. All rights reserved.

S2D120V005E, Rev. 1.1

0

Page 4 of 4

0